

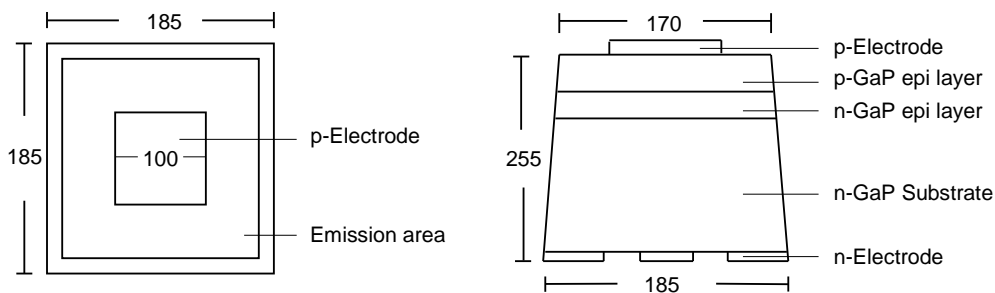
### ■ Features :

- GaP/GaP Epi Wafer

### ■ Typical Applications :

- Lamp
- SMD

### ■ Outline Dimensions : (Unit: um)



### ■ Physical Structure :

Chip dimension	Chip size	185 um x 185 um
	Thickness	255 um
	Emission area	170 um
	Bonding pad	100 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

### ■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	1.90	2.25	2.40	V
Reverse Current	$I_R$	$V_R = 5 \text{ V}$	-	-	10	uA
Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	-	568	-	nm
	Hue		569	572	574	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	30	-	nm
Luminous Intensity	$I_V$	$I_F = 20 \text{ mA}$	8.0	-	-	mcd